

NTE5480 thru NTE5487 Silicon Controlled Rectifier (SCR) 8 Amp, TO64

Description:

The NTE5480 through NTE5487 are multi-purpose PNPN silicon controlled rectifiers in a TO64 type package suited for industrial and consumer applications. These 8 amp devices are available in voltages ranging from 25V to 600V.

Features:

- Uniform Low-Level Noise-Immune Gate Triggering: I_{GT} = 10mA Typ @ T_C = +25°C
- Low Forward "ON" Voltage: v_T = 1V Typ @ 5A @ +25°C
- High Surge-Current Capability: I_{TSM} = 100A Peak
- Shorted Emitter Construction

Absolute Maximum Ratings: $(T_J = -40^\circ \text{ to } +100^\circ \text{C} \text{ unless otherwise specified})$	
Peak Repetitive Forward and Reverse Blocking Voltage (Note 1), V _{DRM} or V _{RRM}	
NTE5480	
NTE5481	
NTE5482	
NTE5483	
NTE5484	
NTE5485	
NTE5486	
NTE5487 (This device is discontinued)	
Forward Current RMS, I _{T(RMS)}	
Peak Forward Surge Current (One Cycle, 60Hz, T _J = -40° to +100°C, I _{TSM}	100A
Circuit Fusing (t \leq 8.3ms, T _J = -40° to $+100^{\circ}$ C), I ² t	40A ² s
Peak Gate Power, P _{GM}	
Average Gate Power, P _{G(AV)}	
Peak Gate Current, I _{GM}	2A
Peak Gate Voltage (Note 2), V _{GM}	10V
Operating Temperature Range, T _J	-40° to $+100^{\circ}$ C
Storage Temperature Range, T _{stq}	-40° to +150°C
Typical Thermal Resistance, Junction-to-Case, RthJC	1.5°C/W
Typical Thermal Resistance, Case-to-Ambient, R _{thJA}	
Note 1. Ratings apply for zero or negative gate voltage. Devices should not be test	sted for blocking

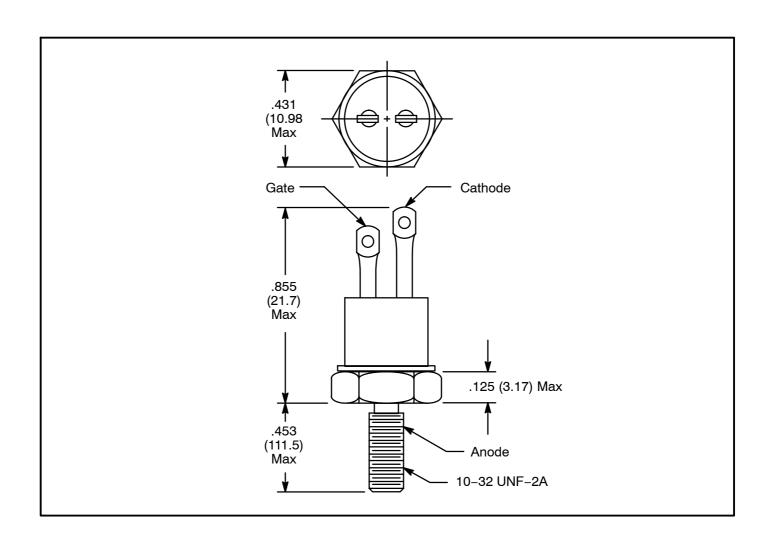
- Note 1. Ratings apply for zero or negative gate voltage. Devices should not be tested for blocking capability in a manner such that the voltage applied exceeds the rated blocking voltage.
- Note 2. Devices should not be operated with a positive bias applied to the gate concurrently with a negative potential applied to the anode.

Electrical Characteristics: $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit
Peak Forward or Reverse Blocking Current	I _{DRM} , I _{RRM}	Rated V _{DRM} or V _{RRM} , Gate Open	T _J = +25°C	_	-	10	μΑ
			T _J = +100°C	_	_	2	mA
Gate Trigger Current (Continuous DC)	I _{GT}	$V_D = 7V$, $R_L = 100\Omega$, Note 3		_	10	30	mA
			$T_C = -40^{\circ}C$	_	-	60	mA
Gate Trigger Voltage (Continuous DC) V ₀	V_{GT}	$V_D = 7V$, $R_L = 100\Omega$		-	0.75	1.5	V
			$T_C = -40^{\circ}C$	_	_	2.5	V
			T _J = +100°C	0.2	-	_	V
Forward "ON" Voltage	ν _{TM}	I _{TM} = 15.7A, Note 4		_	1.4	2.0	V
Holding Current	I _H	V _D = 7V, Gate Open		_	10	30	mA
			T _C = -40°C	_	-	60	mA
Turn-On Time (t _d + t _r)	t _{on}	I_G = 20mA, I_F = 5A, V_D = Rated V_{DRM}		_	1	_	μs
Turn-Off Time	t _{off}	$I_F = 5A$, $I_R = 5A$, $dv/dt = 30V/\mu s$		_	15	_	μs
			$T_J = +100^{\circ}C,$ $V_D = Rated V_{DRM}$	_	25	_	μs
Forward Voltage Application Rate (Exponential)	dv/dt	Gate Open, $T_J = +100$ °C, $V_D = Rated V_{DRM}$		_	50	-	V/μs

Note 3. For optimum operation, i.e. faster turn–on, lower switching losses, best di/dt capability, recommended I_{GT} = 200mA minimum.

Note 4. Pulsed, 1ms max., Duty Cycle \leq 1%.



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SCRs category:

Click to view products by NTE manufacturer:

Other Similar products are found below:

NTE5428 NTE5448 NTE5457 NTE5511 T1500N16TOF VT T720N18TOF T880N14TOF T880N16TOF TS110-7UF TT104N12KOF-A
TT104N12KOF-K TT162N16KOF-A TT162N16KOF-K TT330N16AOF VS-16RIA100 VS-22RIA20 VS-2N5206 VS-2N685 VS40TPS08A-M3 VS-ST230S12P1VPBF 057219R CLB30I1200HB T1190N16TOF VT T1220N22TOF VT T201N70TOH T830N18TOF
TD92N16KOF-A TT250N12KOF-K VS-2N692 VS-2N689 VS-25RIA40 VS-16RIA120 VS-10RIA120 VS-30TPS08PBF NTE5427
NTE5442 VS-2N690 VS-ST300S20P0PBF TT251N16KOF-K VS-22RIA100 VS-16RIA40 CR02AM-8#F00 VS-ST110S12P0VPBF
TD250N16KOF-A VS-ST110S16P0 VS-10RIA10 VS-16TTS08-M3 TS110-7A1-AP T930N36TOF VT T2160N24TOF VT